## NJW0281G (NPN) **NJW0302G (PNP)**

## **Complementary NPN-PNP Power Bipolar Transistors**

These complementary devices are lower power versions of the popular NJW3281G and NJW1302G audio output transistors. With superior gain linearity and safe operating area performance, these transistors are ideal for high fidelity audio amplifier output stages and other linear applications.

### **Features**

- Exceptional Safe Operating Area
- NPN/PNP Gain Matching within 10% from 50 mA to 3 A
- Excellent Gain Linearity
- High BVCEO
- High Frequency
- These Devices are Pb-Free and are RoHS Compliant

- Reliable Performance at Higher Powers
- Symmetrical Characteristics in Complementary Configurations
- Accurate Reproduction of Input Signal
- Greater Dynamic Range
- High Amplifier Bandwidth

## **Applications**

- High-End Consumer Audio Products
  - Home Amplifiers
  - Home Receivers
- Professional Audio Amplifiers
  - Theater and Stadium Sound Systems
  - Public Address Systems (PAs)

## **MAXIMUM RATINGS**

Rating	Symbol	Value	Unit	1 2
Collector-Emitter Voltage	V <sub>CEO</sub>	250	Vdc	3
Collector-Base Voltage	$V_{CBO}$	250	Vdc	xxx G
Emitter-Base Voltage	V <sub>EBO</sub>	5.0	Vdc	1
Collector-Emitter Voltage - 1.5 V	V <sub>CEX</sub>	250	Vdc	EAN-IC.CG W
Collector Current - Continuous	C	15 N	Adc	
Collector Current - Peak (Note 1)	Ісм	30	Adc	OR
Base Current - Continuous	OCEAN	1.5	Adc	
Total Power Dissipation @ T <sub>C</sub> = 25°C	$P_{D}$	150	Watts	Device
Operating and Storage Junction Temperature Range	T <sub>J</sub> , T <sub>stg</sub>	– 65 to +150	°C	NJW0281G

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

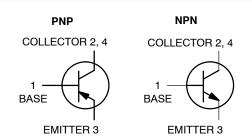
1. Pulse Test: Pulse Width = 5.0 ms, Duty Cycle < 10%.

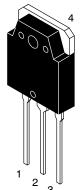


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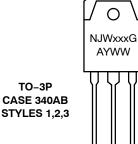
http://onsemi.com

# 15 AMPERES **COMPLEMENTARY SILICON** to 3 A





XXXX



**MARKING** 

**DIAGRAM** 

= 0281 or 0302 = Pb-Free Package = Assembly Location = Year = Work Week

#### **ORDERING INFORMATION**

Device	Package	Shipping
NJW0281G	TO-3P (Pb-Free)	30 Units/Rail
NJW0302G	TO-3P (Pb-Free)	30 Units/Rail

1

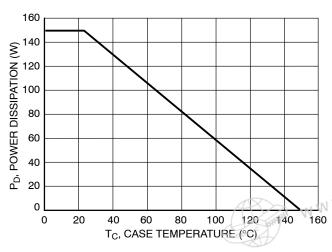
## NJW0281G (NPN) NJW0302G (PNP)

## THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
Thermal Resistance, Junction-to-Case		0.83	°C/W

## **ELECTRICAL CHARACTERISTICS** (T<sub>C</sub> = 25°C unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit
OFF CHARACTERISTICS				
Collector–Emitter Sustaining Voltage ( $I_C = 30 \text{ mA}, I_B = 0$ )	V <sub>CEO(sus)</sub>	250	-	V
Collector Cutoff Current (V <sub>CB</sub> = 250 V, I <sub>E</sub> = 0)	Ісво	-	10	μА
Emitter Cutoff Current (V <sub>EB</sub> = 5.0 V, I <sub>C</sub> = 0)	I <sub>EBO</sub>	-	5.0	μΑ
ON CHARACTERISTICS	c C			
DC Current Gain $ \begin{aligned} &(I_C = 0.5 \text{ A, } V_{CE} = 5.0 \text{ V}) \\ &(I_C = 1.0 \text{ A, } V_{CE} = 5.0 \text{ V}) \\ &(I_C = 3.0 \text{ A, } V_{CE} = 5.0 \text{ V}) \end{aligned} $	√ \ h <sub>FE</sub>	75 75 75	150 150 150	-
Collector–Emitter Saturation Voltage (I <sub>C</sub> = 5.0 A, I <sub>B</sub> = 0.5 A)	V <sub>CE(sat)</sub>	-	1.0	V
Base-Emitter On Voltage (I <sub>C</sub> = 5.0 A, V <sub>CE</sub> = 5.0 V)	V <sub>BE(on)</sub>	-	1.2	V
DYNAMIC CHARACTERISTICS				
Current–Gain – Bandwidth Product ( $I_C = 1.0 \text{ A}, V_{CE} = 5.0 \text{ V}, f_{test} = 1.0 \text{ MHz}$ )	f <sub>T</sub>	30	-	MHz
Output Capacitance (V <sub>CB</sub> = 10 V, I <sub>E</sub> = 0, f <sub>test</sub> = 1.0 MHz)	C <sub>ob</sub>	_	400	pF



100 COPECTOR-EMITTER VOLTAGE (V)

Figure 1. Power Derating

Figure 2. Safe Operating Area

## NJW0281G (NPN) NJW0302G (PNP)

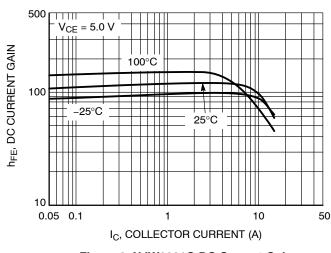


Figure 3. NJW0281G DC Current Gain

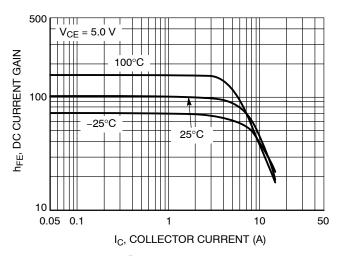


Figure 4. NJW0302G DC Current Gain

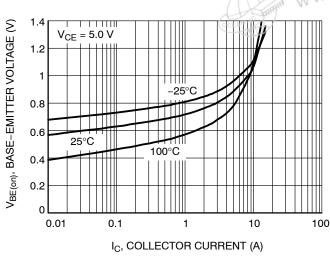


Figure 5. NJW0281G Base-Emitter Voltage

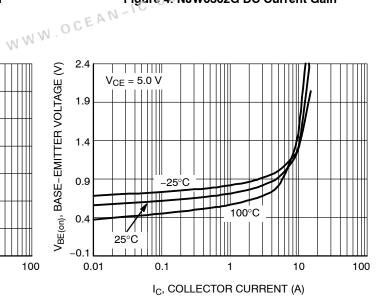


Figure 6. NJW0302G Base-Emitter Voltage

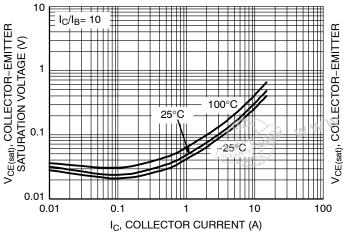


Figure 7. NJW0281G Saturation Voltage

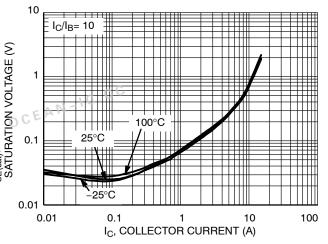


Figure 8. NJW0302G Saturation Voltage

## NJW0281G (NPN) NJW0302G (PNP)

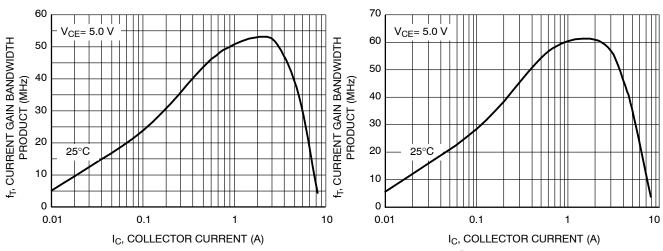


Figure 9. NJW0281G Current Gain Bandwidth
Product

Figu

Figure 10. NJW0302G Current Gain Bandwidth Product

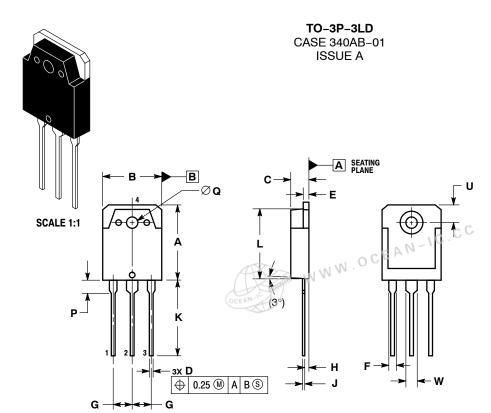


STYLE 1: PIN 1. BASE

2. COLLECTOR

EMITTER

COLLECTOR



STYLE 3:

PIN 1. GATE

2. DRAIN

SOURCE

DRAIN

STYLE 2:

PIN 1.

2.

ANODE CATHODE

CATHODE

ANODE

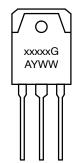
**DATE 30 OCT 2007** 

#### NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994.
- 2 CONTROLLING DIMENSION: MILLIMETERS
  3. DIMENSION & APPLIES TO PLATED TERMINAL
  AND IS MEASURED BETWEEN 0.15 AND 0.30mm FROM THE TERMINAL TIP.
- DIMENSION A AND B DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			
DIM	MIN	NOM	MAX	
Α	19.70	19.90	20.10	
В	15.40	15.60	15.80	
С	4.60	4.80	5.00	
D	0.80	1.00	1.20	
Е	1.45	1.50	1.65	
F	1.80	2.00	2.20	
G	5.45 BSC			
Н	1.20	1.40	1.60	
J	0.55	0.60	0.75	
K	19.80	20.00	20.20	
L	18.50	18.70	18.90	
P	3.30	3.50	3.70	
Q	3.10	3.20	3.50	
U	5.00 REF			
W	2.80	3.00	3.20	

## **GENERIC MARKING DIAGRAM\***



XXXXX = Specific Device Code = Pb-Free Package G = Assembly Location Α

WW = Work Week

\*This information is generic. Please refer to device data sheet for actual part marking. Ph\_Free:

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DESCRIPTION:	TO-3P-3LD		PAGE 1 OF 1	

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